

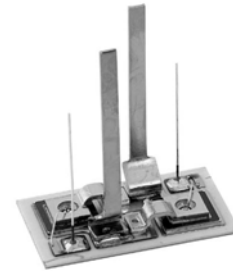
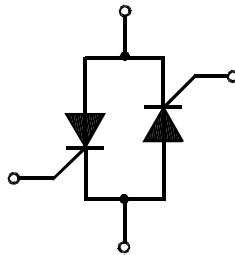
Single Phase AC Controller Subassemblies

PSW1C75

$I_{RMS} = 86 \text{ A}$
 $V_{RRM} = 800-1400 \text{ V}$

Preliminary Data Sheet

V_{RSM} V_{DSM} (V)	V_{RRM} V_{DRM} (V)	Type
900	800	PSW1C 75/08
1300	1200	PSW1C 75/12
1500	1400	PSW1C 75/14



Symbol	Test Conditions	Maximum Ratings
I_{RMS}	$T_C = 85^\circ\text{C}; 50-400\text{Hz (per phase)}$	86 A
I_{TAVM}	$T_C = 85^\circ\text{C}; 180^\circ \text{ sine}$	39 A
I_{TSM}	$T_{VJ} = 45^\circ\text{C}$ $t = 10 \text{ ms}$ (50 Hz), sine	1000 A
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1100 A
	$T_{VJ} = 125^\circ\text{C}$ $t = 10 \text{ ms}$ (50 Hz), sine	900 A
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	1000 A
$\int i^2 dt$	$T_{VJ} = 45^\circ\text{C}$ $t = 10 \text{ ms}$ (50 Hz), sine	5000 A ² s
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	5020 A ² s
	$T_{VJ} = 125^\circ\text{C}$ $t = 10 \text{ ms}$ (50 Hz), sine	4050 A ² s
	$V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	4150 A ² s
$(di/dt)_{cr}$	$T_{VJ} = 125^\circ\text{C}$ repetitive, $I_T = 150 \text{ A}$ $f=50\text{Hz}, t_p=200\mu\text{s}$	150 A/ μs
	$V_D=2/3V_{DRM}$	
	$I_G=0.45 \text{ A}$ non repetitive, $I_T = I_{TAVM}$ $di_G/dt=0.45\text{A}/\mu\text{s}$	500 A/ μs
$(dv/dt)_{cr}$	$T_{VJ} = 125^\circ\text{C}$ $V_D=2/3V_{DRM}$ $R_{GK} = \infty$, method 1 (linear voltage rise)	1000 V/ μs
P_{GM}	$T_{VJ} = 125^\circ\text{C}$ $t_p=30\mu\text{s}$	$\leq 10 \text{ W}$
	$I_T=I_{TAVM}$ $t_p=300\mu\text{s}$	$\leq 5 \text{ W}$
P_{GAVM}		0.5 W
V_{RGM}		10 V
T_{VJ}		-40... + 125 °C
T_{VJM}		125 °C
T_{stg}		-40... + 125 °C
Weight	typ.	9 g

Features

- Planar glass passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering

Applications

- Solid state relays

Advantages

- Space and weight savings
- Improved temperature and power cycling capability
- High power density
- Small and light weight

Data according to IEC 60747 refer to a single thyristor unless otherwise stated

Symbol	Test Conditions	Characteristic Value
$I_{D,R}$	$T_{VJ} = 125^{\circ}\text{C}$, $V_R = V_{RRM}$, $V_D = V_{DRM}$	≤ 5 mA
V_T	$I_T = 200$ A, $T_{VJ} = 25^{\circ}\text{C}$	≤ 1.55 V
V_{TO}	For power-loss calculations only	0.85 V
r_T		4.0 m Ω
V_{GT}	$V_D = 6\text{V}$, $T_{VJ} = 25^{\circ}\text{C}$	≤ 1.5 V
	$T_{VJ} = -40^{\circ}\text{C}$	≤ 1.6 V
I_{GT}	$V_D = 6\text{V}$, $T_{VJ} = 25^{\circ}\text{C}$	≤ 100 mA
	$T_{VJ} = -40^{\circ}\text{C}$	≤ 200 mA
V_{GD}	$T_{VJ} = 125^{\circ}\text{C}$, $V_D = 2/3V_{DRM}$	≤ 0.2 V
I_{GD}	$T_{VJ} = 125^{\circ}\text{C}$, $V_D = 2/3V_{DRM}$	≤ 10 mA
I_L	$T_{VJ} = 25^{\circ}\text{C}$, $t_p = 10\mu\text{s}$, $V_D = 6\text{V}$ $I_G = 0.45\text{A}$, $di_G/dt = 0.45\text{A}/\mu\text{s}$	≤ 450 mA
I_H	$T_{VJ} = 25^{\circ}\text{C}$, $V_D = 6\text{V}$, $R_{GK} = \infty$	≤ 200 mA
t_{gd}	$T_{VJ} = 25^{\circ}\text{C}$, $V_D = 1/2V_{DRM}$ $I_G = 0.45\text{A}$, $di_G/dt = 0.45\text{A}/\mu\text{s}$	≤ 2 μs
t_q	$T_{VJ} = T_{VJM}$; $I_T = 120\text{A}$; $t_p = 200\mu\text{s}$; $-di/dt = 10\text{A}/\mu\text{s}$ typ. 150	μs
	$V_R = 100\text{V}$; $dv/dt = 20\text{V}/\mu\text{s}$; $V_D = 2/3V_{DRM}$	
R_{thJC}	per thyristor; DC	0.8 K/W
	per module	0.4 K/W
a	Max. allowable acceleration	50 m/s ²

Package style and outline

Dimensions in mm (1mm = 0.0394")

